



# PSMN6R5-80BS

N-channel 80V 6.9mΩ standard level MOSFET in D2PAK

Rev. 1 — 21 October 2011

Objective data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

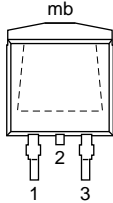
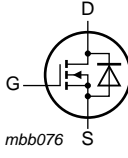
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a> <sup>[1]</sup>	-	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	210	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C};$ see <a href="#">Figure 13</a>	-	5.9	6.9	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 40\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	16	-	nC
$Q_{G(tot)}$	total gate charge		-	71	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; I_D = 49\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ Ω};$ unclamped	-	-	700	mJ

[1] Continuous current rating is limited by package.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT404 (D2PAK)**

[1] It is not possible to make connection to pin 2.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R5-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

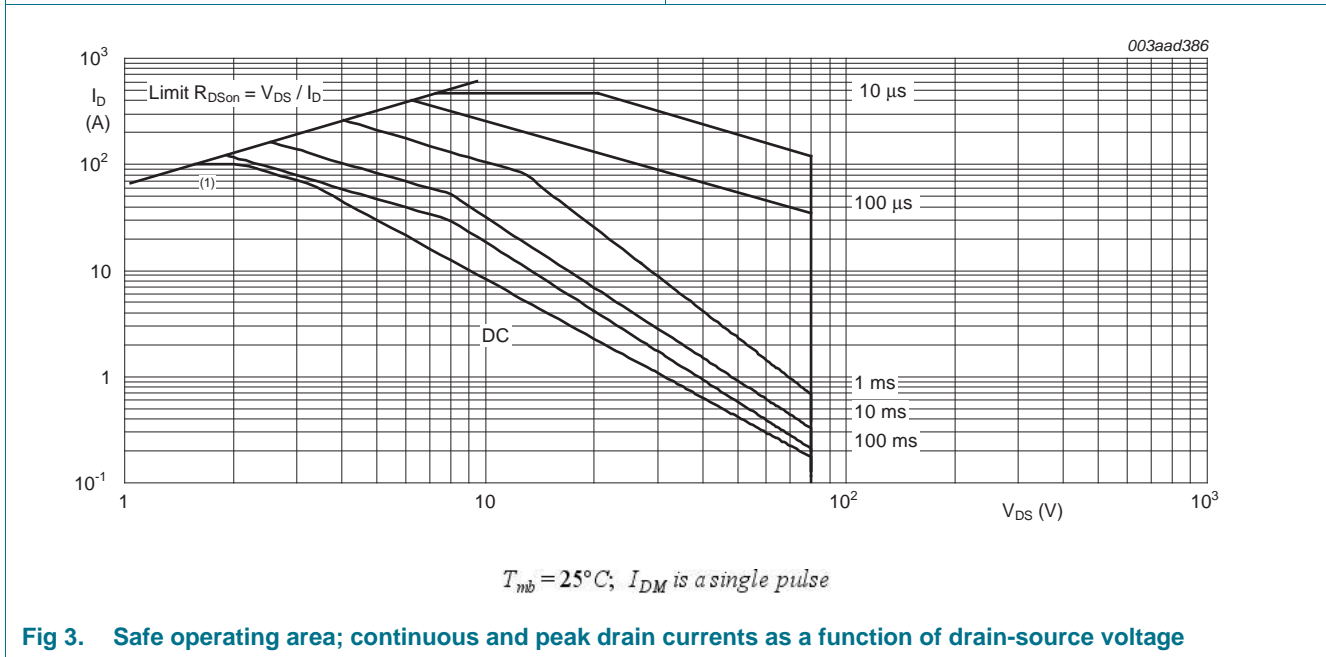
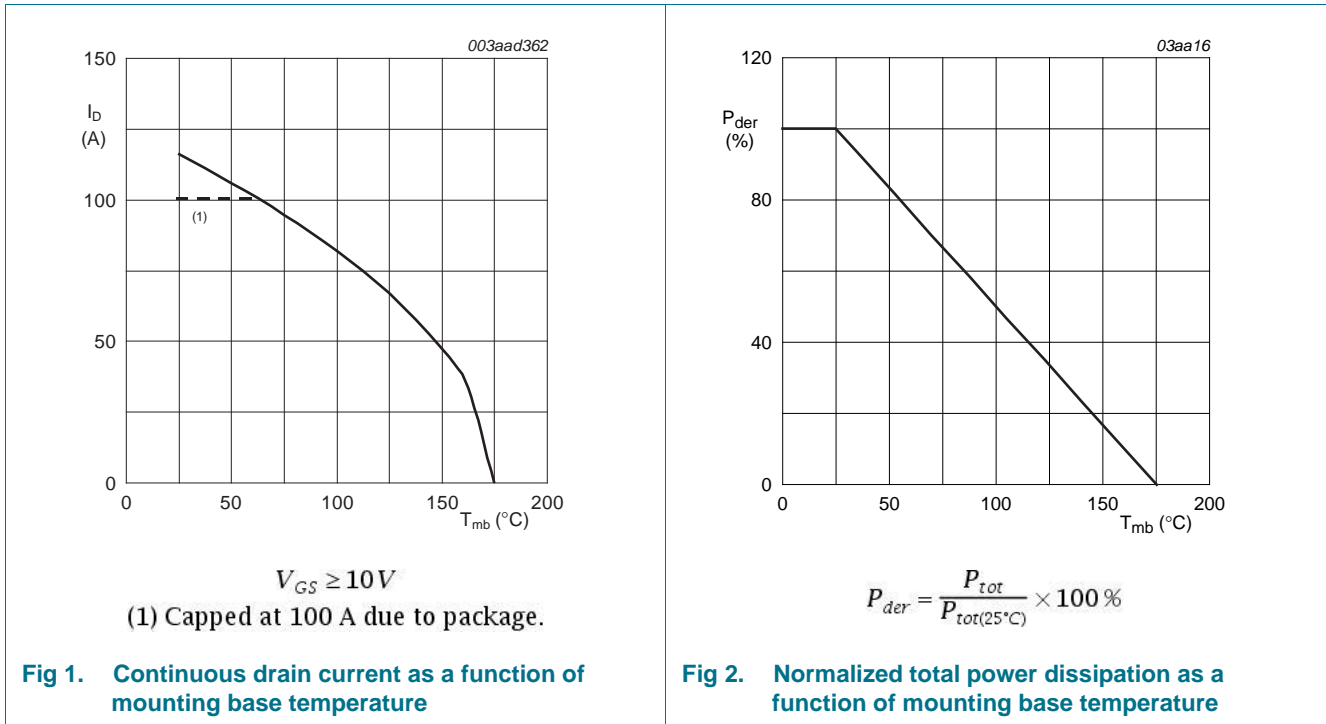
## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	80	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	80	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	82	A
		$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	100	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	470	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	210	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	100	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	470	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 49\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped	-	700	mJ

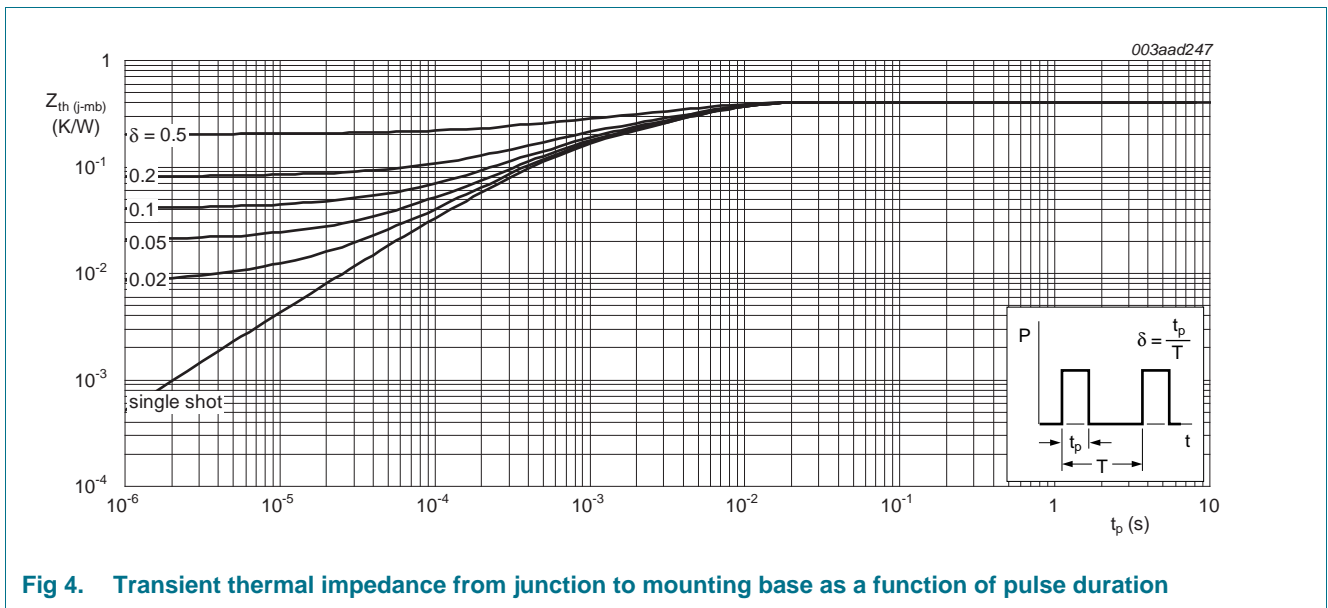
[1] Continuous current rating is limited by package.



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	0.4	0.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



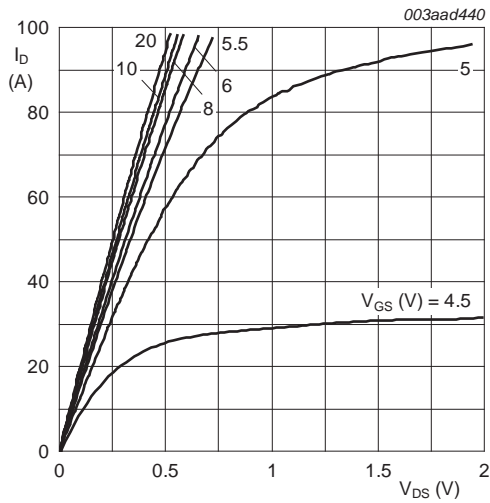
## 6. Characteristics

**Table 6. Characteristics**
*Tested to JEDEC standards where applicable.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ\text{C}$	73	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2.3	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	0.3	10	$\mu A$
		$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 125 \text{ }^\circ\text{C}$	-	-	150	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 15 A; T_j = 100 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	-	11.5	mΩ
		$V_{GS} = 10 V; I_D = 15 A; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	-	16.56	mΩ
		$V_{GS} = 10 V; I_D = 15 A; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	5.9	6.9	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	0.75	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	61	-	nC
		$I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V;$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	71	-	nC
$Q_{GS}$	gate-source charge		-	19	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	13.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	5.8	-	nC
$Q_{GD}$	gate-drain charge		-	16	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 A; V_{DS} = 40 V;$ see <a href="#">Figure 15</a>	-	4.3	-	V
$C_{iss}$	input capacitance	$V_{DS} = 40 V; V_{GS} = 0 V; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>	-	4461	-	pF
$C_{oss}$	output capacitance		-	410	-	pF
$C_{rss}$	reverse transfer capacitance		-	214	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40 V; R_L = 0.5 \text{ } \Omega; V_{GS} = 10 V;$ $R_{G(ext)} = 4.7 \text{ } \Omega$	-	26	-	ns
$t_r$	rise time		-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	57	-	ns
$t_f$	fall time		-	22	-	ns

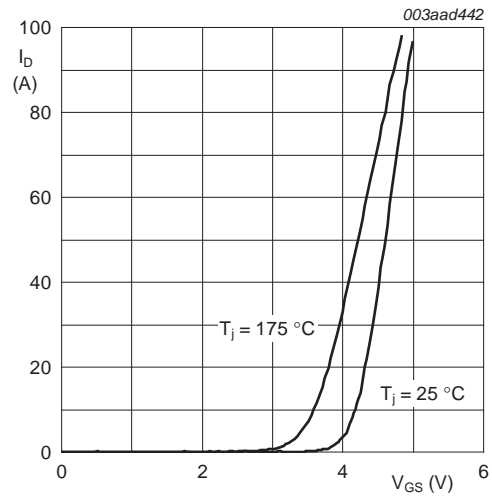
**Table 6. Characteristics ...continued**  
 Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 17</a>	-	0.79	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = 100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;	-	48	-	ns
$Q_r$	recovered charge	$V_{DS} = 40\text{ V}$	-	82	-	nC



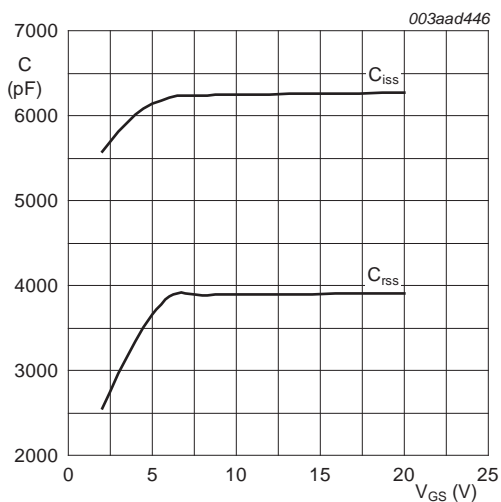
$T_j = 25\text{ °C}$ ;  $t_p = 300\mu\text{s}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



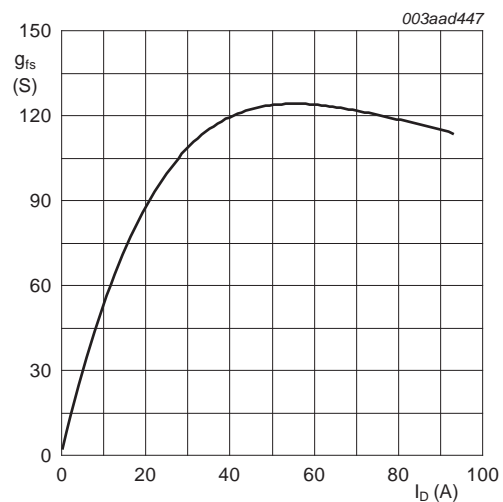
$V_{DS} = 15\text{ V}$

**Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



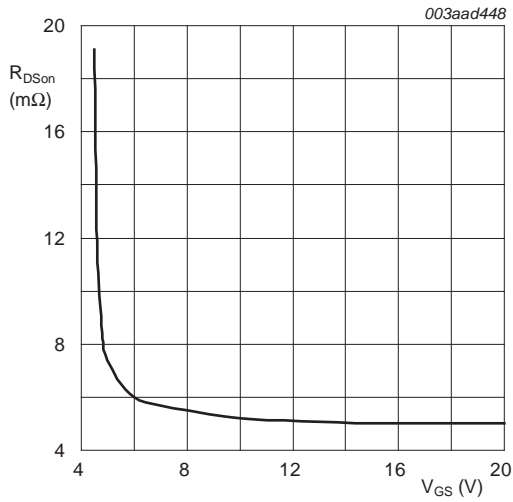
$V_{DS} = 0\text{ V}$ ;  $f = 1\text{ MHz}$

**Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values**



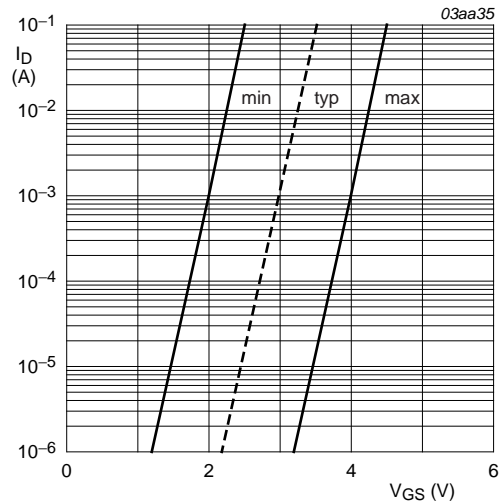
$T_j = 25\text{ °C}$ ;  $V_{DS} = 15\text{ V}$

**Fig 8. Forward transconductance as a function of drain current; typical values**



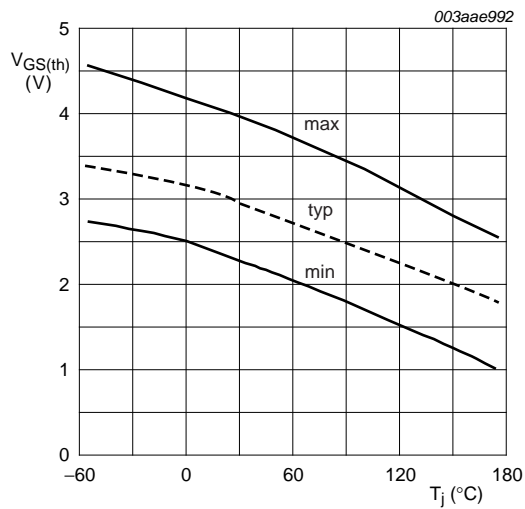
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



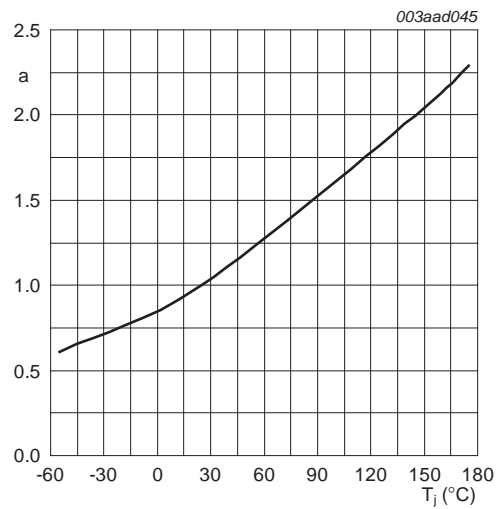
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



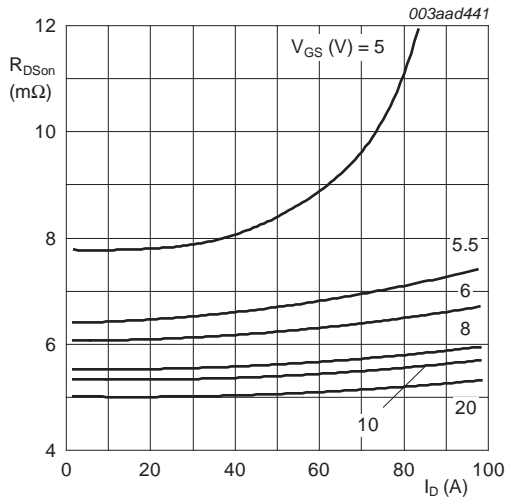
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^\circ C; t_p = 300 \mu s$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

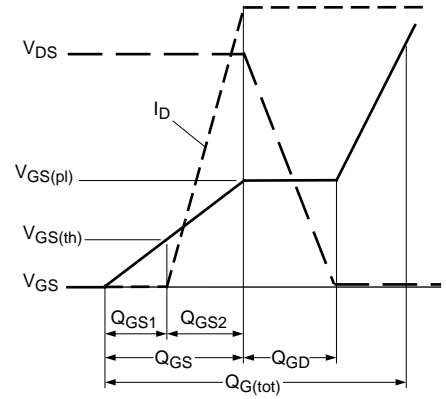
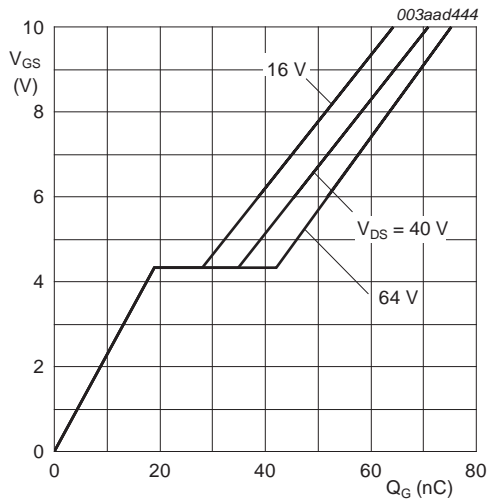
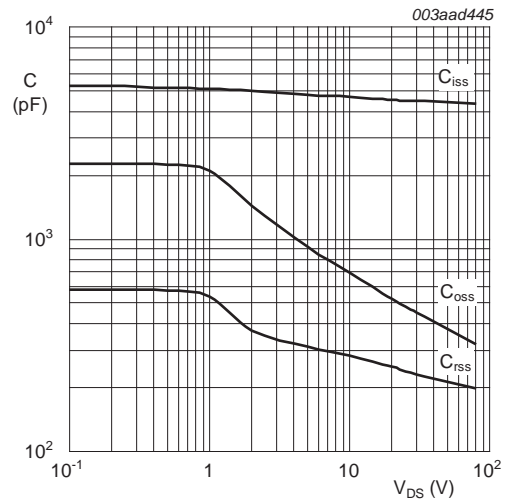


Fig 14. Gate charge waveform definitions



$T_j = 25^\circ C; I_D = 25 A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 V; f = 1 MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



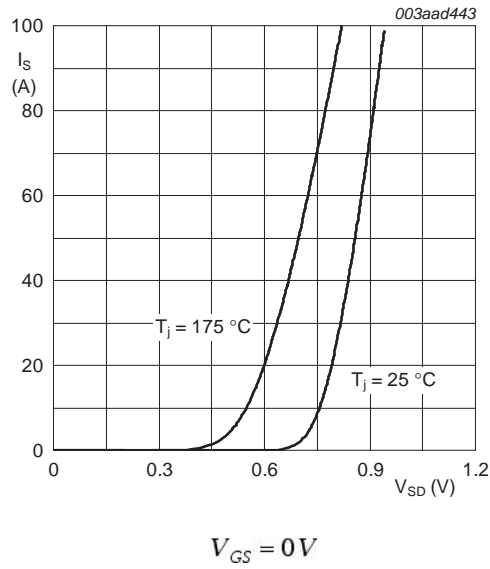


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



Fig 18. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R5-80BS v.1	20111021	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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